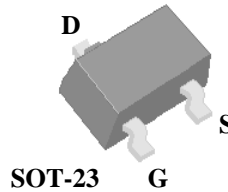


- ▼ Simple Drive Requirement
- ▼ Small Package Outline
- ▼ ESD Diode Protected
- ▼ RoHS Compliant & Halogen-Free

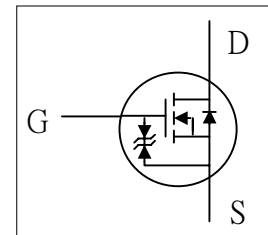


$BV_{DSS}$	600V
$R_{DS(ON)}$	72 $\Omega$
$I_D$	53mA
HBM ESD	2KV

### Description

XP60PN72 series are innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The special design SOT-23 package with good thermal performance is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.



### Absolute Maximum Ratings @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_A=25^\circ\text{C}$	Drain Current <sup>3</sup> , $V_{GS}$ @ 10V	53	mA
$I_D @ T_A=70^\circ\text{C}$	Drain Current <sup>3</sup> , $V_{GS}$ @ 10V	43	mA
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	300	mA
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation	0.5	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	250	$^\circ\text{C}/\text{W}$

**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	600	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =50mA	-	-	72	Ω
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	-	5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =50mA	-	200	-	mS
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =480V, V <sub>GS</sub> =0V	-	-	100	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±30	uA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =0.1A	-	2.5	4	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =200V	-	1	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =10V	-	0.3	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =300V	-	10	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =50mA	-	8	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	14	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =10V	-	77	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	50	80	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =100V	-	9	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	5	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =0.05A, V <sub>GS</sub> =0V	-	-	1.5	V

**Notes:**

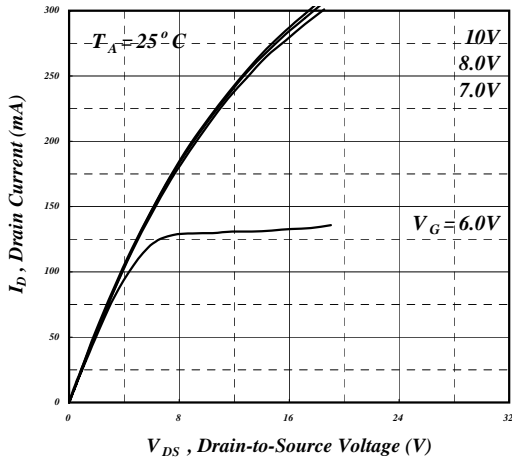
- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Mounted on min. copper pad FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

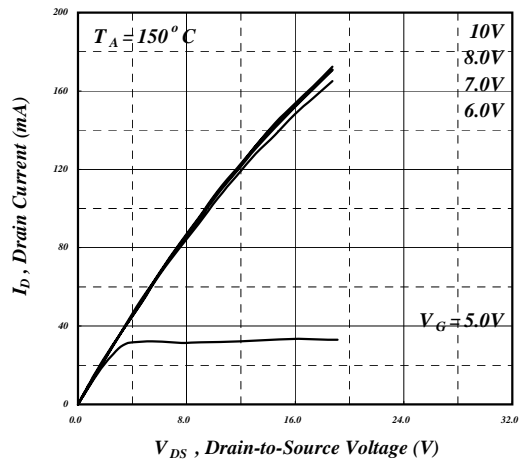
USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

XSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

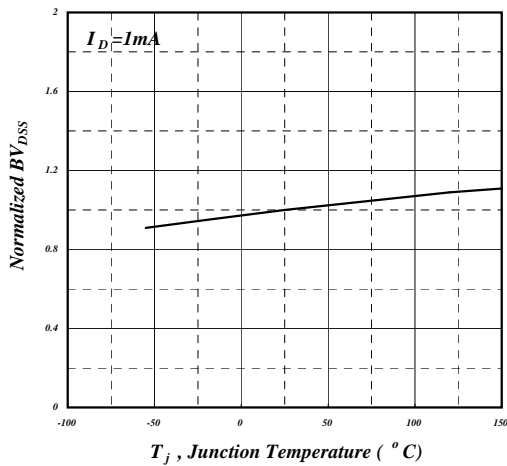
XSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.



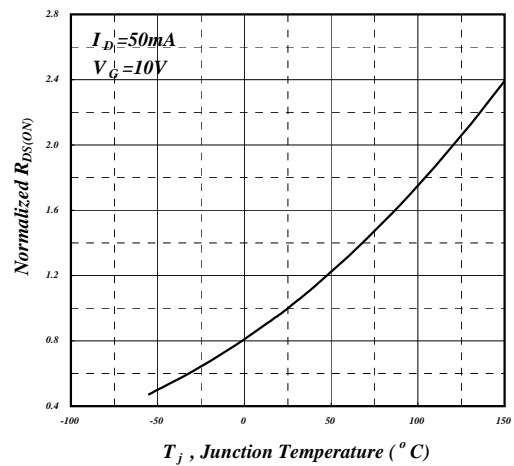
**Fig 1. Typical Output Characteristics**



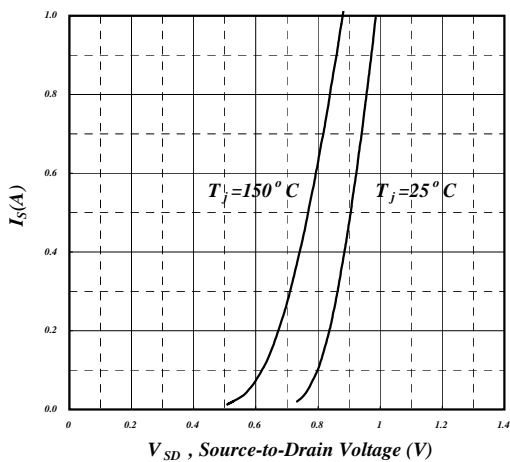
**Fig 2. Typical Output Characteristics**



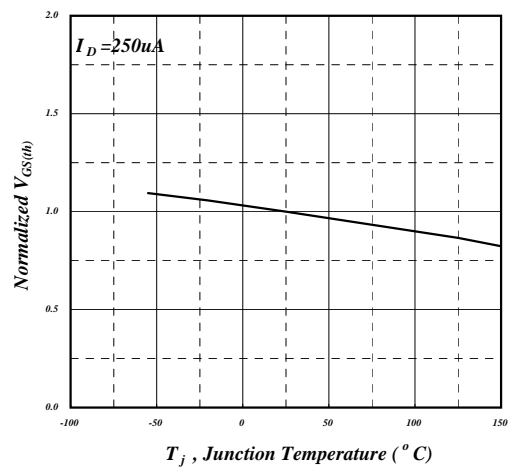
**Fig 3. Normalized  $BV_{DS}$  v.s. Junction Temperature**



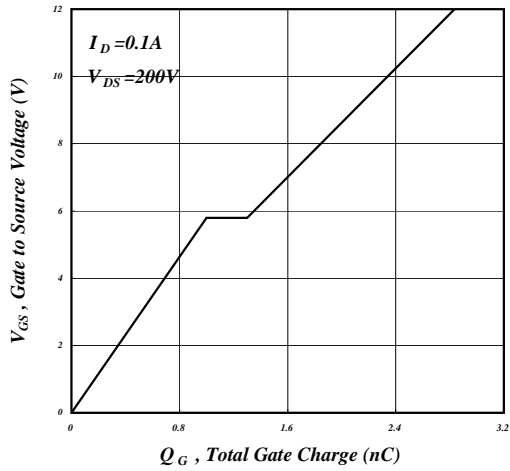
**Fig 4. Normalized On-Resistance v.s. Junction Temperature**



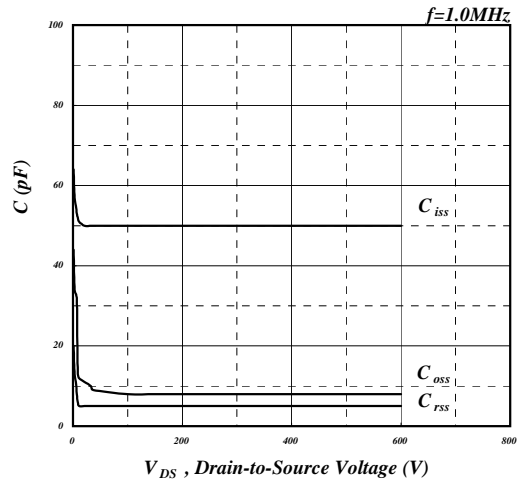
**Fig 5. Forward Characteristic of Reverse Diode**



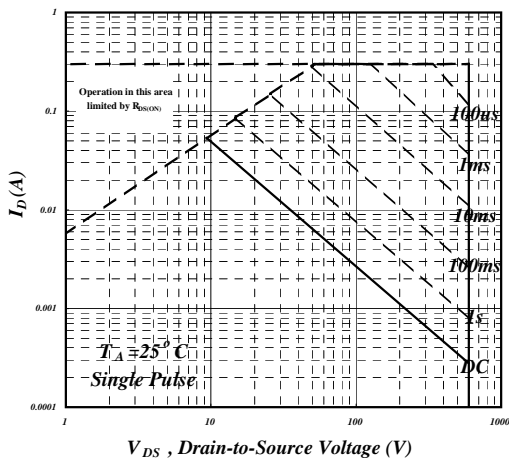
**Fig 6. Gate Threshold Voltage v.s. Junction Temperature**



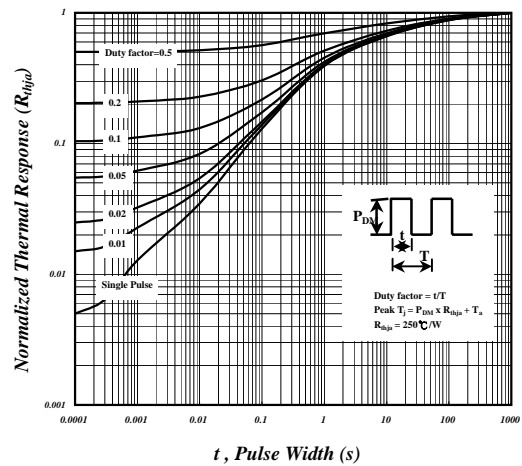
**Fig 7. Gate Charge Characteristics**



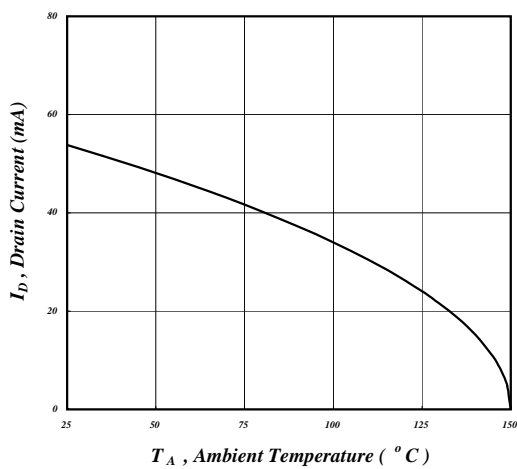
**Fig 8. Typical Capacitance Characteristics**



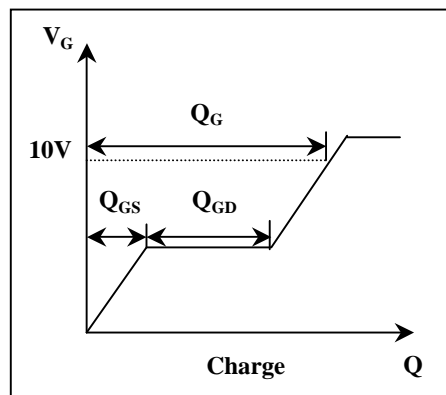
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**



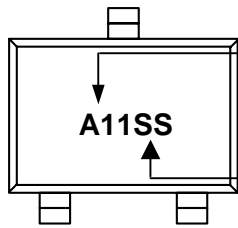
**Fig 11. Drain Current v.s. Ambient Temperature**



**Fig 12. Gate Charge Circuit**

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**MARKING INFORMATION**



Part Number : A11

Date Code : SS

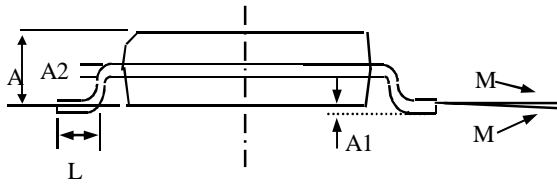
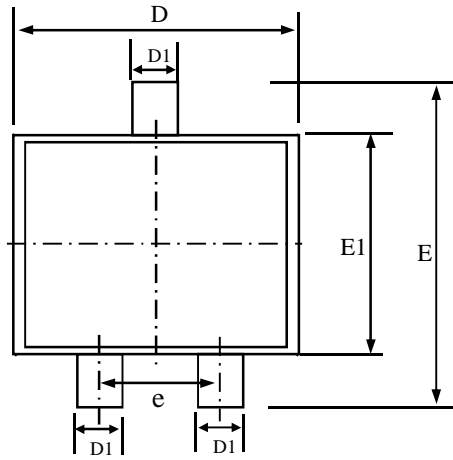
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SS:2002,2006,2010,2014,2018,2022...

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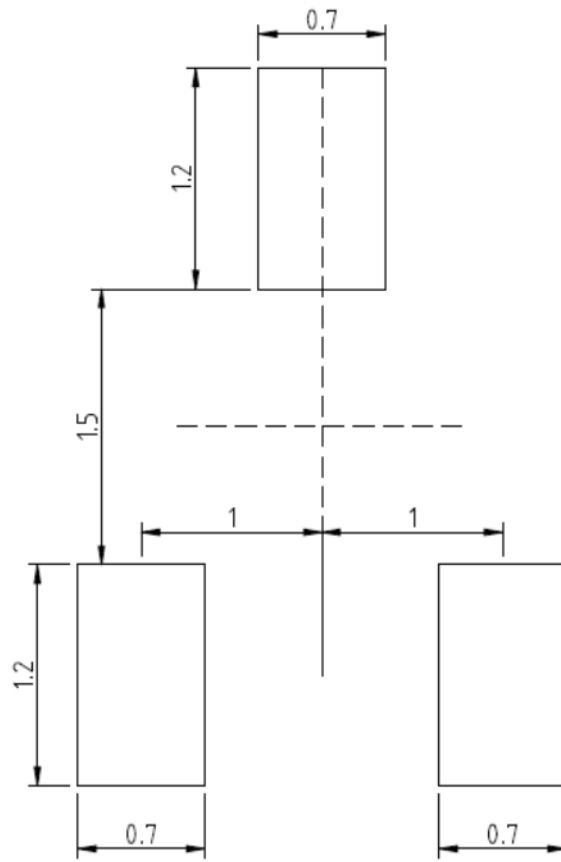
**Package Outline : SOT-23**



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	0.90	1.08	1.25
A1	0.00	0.08	0.15
A2	0.08	0.17	0.25
D1	0.30	0.40	0.50
e	1.70	2.00	2.30
D	2.70	2.90	3.10
E	2.40	2.70	3.00
E1	1.40	1.60	1.80
M	0°	5°	10°
L	0.30	0.45	0.60

1. All Dimension Are In Millimeters.
2. Dimension Does Not Include Mold Protrusions.
3. Does not Contain Dam Bar Dimension.

**SOT-23 FOOTPRINT :**



UNIT: mm